L A Coldren

List of Publications by Year
in descending order

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163	7,168	57631	62479
papers	citations	44 h-index	80 g-index

164	164	164	3706
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Power-Efficient Kerr Frequency Comb Based Tunable Optical Source. IEEE Photonics Journal, 2017, 9, 1-14.	1.0	14
2	Single-chip dual-pumped SOA-based phase-sensitive amplifier at 1550nm. , 2015, , .		2
3	Fully integrated hybrid silicon two dimensional beam scanner. Optics Express, 2015, 23, 5861.	1.7	262
4	30 Gbps bottom-emitting 1060 nm VCSEL. , 2014, , .		1
5	Fully integrated hybrid silicon free-space beam steering source with 32-channel phased array. Proceedings of SPIE, 2014, , .	0.8	12
6	Hybrid silicon free-space source with integrated beam steering. Proceedings of SPIE, 2013, , .	0.8	2
7	An Integrated 40 Gbit/s Optical Costas Receiver. Journal of Lightwave Technology, 2013, 31, 2244-2253.	2.7	44
8	Two-Dimensional Optical Beam Steering With InP-Based Photonic Integrated Circuits. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 6100212-6100212.	1.9	66
9	High-performance InP/GaAs based photonic integrated circuits. , 2013, , .		1
10	Hybrid III/V silicon photonic source with integrated 1D free-space beam steering. Optics Letters, 2012, 37, 4257.	1.7	53
11	Two-dimensional free-space beam steering with an optical phased array on silicon-on-insulator. Optics Express, 2011, 19, 21595.	1.7	350
12	Externally Mode-Matched Cavity Quantum Electrodynamics with Charge-Tunable Quantum Dots. Physical Review Letters, 2009, 102, 097403.	2.9	67
13	Picosecond Coherent Optical Manipulation of a Single Electron Spin in a Quantum Dot. Science, 2008, 320, 349-352.	6.0	473
14	Introduction to the Issue on Semiconductor Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2007, 13, 1043-1045.	1.9	0
15	Optically detected coherent spin dynamics of a single electron in a quantum dot. Nature Physics, 2007, 3, 770-773.	6.5	121
16	Nondestructive Optical Measurements of a Single Electron Spin in a Quantum Dot. Science, 2006, 314, 1916-1920.	6.0	180
17	Fabrication and molecular beam epitaxy regrowth of first-order, high contrast AlGaAsâˆ•GaAs gratings. Journal of Vacuum Science & Technology B, 2006, 24, 1559.	1.3	2
18	Terahertz-optical mixing in undoped and doped GaAs quantum wells: From excitonic to electronic intersubband transitions. Physical Review B, 2005, 72, .	1.1	12

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19	High-differential-quantum-efficiency, long-wavelength vertical-cavity lasers using five-stage bipolar-cascade active regions. Applied Physics Letters, 2005, 86, 211104.	1.5	9
20	Terahertz electro-optic wavelength conversion in GaAs quantum wells: Improved efficiency and room-temperature operation. Applied Physics Letters, 2004, 84, 840-842.	1.5	37
21	A monolithic diode laser chemical sensor with a quasi-symmetrical sensing waveguide for improved sensitivity. Applied Physics Letters, 2004, 85, 320-322.	1.5	4
22	Terahertz optical mixing in biasedGaAssingle quantum wells. Physical Review B, 2004, 70, .	1.1	16
23	Selectively etched tunnel junction for lateral current and optical confinement in InP-based vertical cavity lasers. Journal of Electronic Materials, 2004, 33, 118-122.	1.0	6
24	Strong-field terahertz optical mixing in excitons. Physical Review B, 2003, 67, .	1.1	18
25	Al0.95Ga0.05As0.56Sb0.44 for lateral oxide-confinement layer in InP-based devices. Applied Physics Letters, 2003, 82, 1329-1331.	1.5	6
26	Molecular-beam epitaxy growth of high-quality active regions with strained InxGa1â^'xAs quantum wells and lattice-matched AlxGayIn(1â^'xâ^'y)As barriers using submonolayer superlattices. Applied Physics Letters, 2002, 80, 3509-3511.	1.5	14
27	Voltage-controlled wavelength conversion by terahertz electro-optic modulation in double quantum wells. Applied Physics Letters, 2002, 81, 1564-1566.	1.5	33
28	Chemical Mechanical Polishing of Gallium Nitride. Electrochemical and Solid-State Letters, 2002, 5, G61.	2.2	63
29	Rate equations of vertical-cavity semiconductor optical amplifiers. Applied Physics Letters, 2002, 80, 3057-3059.	1.5	5
30	88â€ŠÂ°C, continuous-wave operation of apertured, intracavity contacted, 1.55 Î¼m vertical-cavity surface-emitting lasers. Applied Physics Letters, 2001, 78, 1337-1339.	1.5	49
31	Recent Developments in Long-Wavelength VCSELs. , 2001, , .		0
32	Increased lateral oxidation rates of AlInAs on InP using short-period superlattices. Journal of Electronic Materials, 2000, 29, 1100-1104.	1.0	8
33	Molecular beam epitaxial growth of monolithic 1.55 Î¼m vertical cavity surface emitting lasers with AlGaAsSb/AlAsSb Bragg mirrors. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 1601.	1.6	8
34	Improved characteristics of InGaN multiple-quantum-well laser diodes grown on laterally epitaxially overgrown GaN on sapphire. Applied Physics Letters, 2000, 76, 529-531.	1.5	59
35	Near-room-temperature continuous-wave operation of multiple-active-region 1.55 Î¼m vertical-cavity lasers with high differential efficiency. Applied Physics Letters, 2000, 77, 3137-3139.	1.5	41
36	Enhanced wavelength tuning of an InGaAsP-InP laser with a thermal-strain-magnifying trench. Applied Physics Letters, 2000, 77, 2629-2631.	1.5	8

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37	Measured and calculated radiative lifetime and optical absorption ofInxGa1â^'xN/GaNquantum structures. Physical Review B, 2000, 61, 10994-11008.	1.1	137
38	Individually optimized bottom-emitting vertical-cavity lasers and bottom-illuminated resonant photodetectors sharing the same epitaxial structure. Journal of Optics, 1999, 1, 317-319.	1.5	5
39	Epitaxially-stacked multiple-active-region 1.55Î¼m lasers for increased differential efficiency. Applied Physics Letters, 1999, 74, 3251-3253.	1.5	54
40	Effect of AlGaN/GaN Strained Layer Superlattice Period on InGaN MQW Laser Diodes. Physica Status Solidi A, 1999, 176, 59-62.	1.7	10
41	Design parameters for lateral carrier confinement in quantum-dot lasers. Applied Physics Letters, 1999, 74, 2752-2754.	1.5	38
42	Indium tin oxide contacts to gallium nitride optoelectronic devices. Applied Physics Letters, 1999, 74, 3930-3932.	1.5	226
43	Free-Space Optical Interconnect Using Flip-Chip Bonded, Microlensed Arrays of Monolithic Vertical Cavity Lasers and Resonant Photodetectors. , 1999, , .		1
44	Vertical Cavity Lasers with Large Bandwidths at Low Currents for Dense Free-Space Optical Interconnects. , 1999, , .		0
45	Effective band gap inhomogeneity and piezoelectric field in InGaN/GaN multiquantum well structures. Applied Physics Letters, 1998, 73, 2006-2008.	1.5	427
46	Minimum temperature sensitivity of 1.55 Î¼m vertical-cavity lasers at â^'30â€‰nm gain offset. Applied Physics Letters, 1998, 72, 1814-1816.	1.5	76
47	Parallel free-space optical interconnect based on arrays of vertical-cavity lasers and detectors with monolithic microlenses. Applied Optics, 1998, 37, 2811.	2.1	62
48	Measurement of the AlGaInAs/AlGaAs conduction-band offset using ballistic electron emission spectroscopy. Applied Physics Letters, 1998, 73, 3271-3272.	1.5	4
49	Measurement of gain current relations for InGaN multiple quantum wells. Applied Physics Letters, 1998, 73, 3887-3889.	1.5	9
50	Catastrophic optical damage in GaInN multiple quantum wells. Applied Physics Letters, 1998, 72, 3267-3269.	1.5	9
51	Effects of Si-doping in the barriers of InGaN multiquantum well purplish-blue laser diodes. Applied Physics Letters, 1998, 73, 496-498.	1.5	66
52	Technique for integration of vertical cavity lasers and resonant photodetectors. Applied Physics Letters, 1998, 73, 1-3.	1.5	50
53	Surface energy model for the thickness dependence of the lateral oxidation of AlAs. Journal of Applied Physics, 1997, 82, 2277-2280.	1.1	51
54	Reconfigurable optical properties in InGaN/GaN quantum wells. Applied Physics Letters, 1997, 71, 1455-1457.	1.5	13

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55	Coupled-cavity resonant photodetectors for high-performance wavelength demultiplexing applications. Applied Physics Letters, 1997, 71, 178-180.	1.5	12
56	Gain spectroscopy on InGaN/GaN quantum well diodes. Applied Physics Letters, 1997, 70, 2580-2582.	1.5	60
57	Reduced lateral carrier diffusion for improved miniature semiconductor lasers. Journal of Applied Physics, 1997, 81, 3377-3381.	1.1	20
58	Resonant-cavity InGaAs/InAlGaAs/InP photodetector arrays for wavelength demultiplexing applications. Applied Physics Letters, 1997, 70, 2347-2349.	1.5	20
59	Photoluminescence characteristics of GaN/lnGaN/GaN quantum wells. Journal of Electronic Materials, 1997, 26, 325-329.	1.0	2
60	Growth and characterization of bulk InGaN films and quantum wells. Applied Physics Letters, 1996, 68, 3147-3149.	1.5	156
61	Vertical-cavity surface-emitting lasers for free-space interconnects. , 1996, 10284, 8.		5
62	Molecular beam epitaxial growth of strained AlGalnAs multi-quantum well lasers on InP. Journal of Electronic Materials, 1996, 25, 948-954.	1.0	4
63	InP-based multiple quantum well structures grown with tertiarybutylarsine (TBA) and tertiarybutylphosphine (TBP): Effects of growth interruptions on structural and optical properties. Journal of Electronic Materials, 1996, 25, 965-971.	1.0	3
64	Estimation of scattering losses in dielectrically apertured vertical cavity lasers. Applied Physics Letters, 1996, 68, 1757-1759.	1.5	73
65	Dielectric apertures as intracavity lenses in verticalâ€cavity lasers. Applied Physics Letters, 1996, 68, 313-315.	1.5	39
66	Effects of surface recombination on carrier distributions and device characteristics. Journal of Applied Physics, 1995, 78, 3208-3215.	1.1	3
67	Calibrated intensity noise measurements in microcavity laser diodes. Applied Physics Letters, 1995, 67, 3697-3699.	1.5	24
68	Intensity noise and facet correlation in Fabryâ€“PÃ©rot laser diodes with low facet reflectivities. Applied Physics Letters, 1995, 66, 3419-3421.	1.5	5
69	Temperatureâ€dependent threshold and modulation characteristics in InGaAs/GaAs quantumâ€well ridgeâ€waveguide lasers. Applied Physics Letters, 1995, 66, 2040-2042.	1.5	21
70	Surface migration induced selfâ€aligned InAs islands grown by molecular beam epitaxy. Applied Physics Letters, 1995, 66, 1620-1622.	1.5	180
71	Low regrowthâ€“interface recombination rates in InGaAsâ€“GaAs buried ridge lasers fabricated by in situ processing. Applied Physics Letters, 1995, 66, 1966-1968.	1.5	15
72	Evaluating the effects of optical and carrier losses in etchedâ€post vertical cavity lasers. Journal of Applied Physics, 1995, 78, 5871-5875.	1.1	44

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73	Many body effects in the temperature dependence of threshold in a verticalâ€cavity surfaceâ€emitting laser. Applied Physics Letters, 1995, 66, 2460-2462.	1.5	25
74	High modulation efficiency of intracavity contacted vertical cavity lasers. Applied Physics Letters, 1994, 65, 1483-1485.	1.5	50
75	Lateral carrier diffusion and surface recombination in InGaAs/AlGaAs quantumâ€well ridgeâ€waveguide lasers. Journal of Applied Physics, 1994, 76, 4479-4487.	1.1	66
76	Highâ€efficiency and lowâ€threshold InGaAs/AlGaAs quantumâ€well lasers. Journal of Applied Physics, 1994, 76, 3932-3934.	1.1	27
77	Tertiarybutylarsine and tertiarybutylphosphine for the MOCVD growth of low threshold 1.55 Î¼m InxGa1-xAs/InP quantum-well lasers. Journal of Electronic Materials, 1994, 23, 87-91.	1.0	23
78	Widely-Tunable and Vertical-Cavity Lasers: DBRs on Different Planes. , 1994, , .		0
79	Design, fabrication and characterization of high-speed asymmetric Fabry-Perot modulators for optical interconnect applications. Optical and Quantum Electronics, 1993, 25, S885-S898.	1.5	12
80	Guide/antiguide optical intensity modulator. Optical and Quantum Electronics, 1993, 25, S899-S915.	1.5	0
81	Effects of Hydrogen on Chlorine Radicalâ€Beam Ionâ€Beam Etching of Al x Ga1â€‰â^'â€‰x As with Varying Mole Fraction. Journal of the Electrochemical Society, 1993, 140, 1802-1804.	1.3	3
82	Photonic integrated tunable receivers with optical preamplifiers for direct detection. Applied Physics Letters, 1993, 63, 880-882.	1.5	18
83	Bandâ€gap engineered digital alloy interfaces for lower resistance verticalâ€cavity surfaceâ€emitting lasers. Applied Physics Letters, 1993, 63, 3411-3413.	1.5	93
84	Modeling the current to light characteristics of indexâ€guided verticalâ€cavity surfaceâ€emitting lasers. Applied Physics Letters, 1993, 62, 1050-1052.	1.5	28
85	Optical gain anisotropy in serpentine superlattice nanowireâ€array lasers. Applied Physics Letters, 1993, 63, 2015-2017.	1.5	19
86	Large and small signal dynamics of vertical cavity surface emitting lasers. Applied Physics Letters, 1993, 62, 325-327.	1.5	87
87	Characterization of geometric effects for the guide/antiguide intensity modulator. Journal of Applied Physics, 1992, 72, 4455-4457.	1.1	0
88	Effect of layer thickness variations on the performance of asymmetric Fabryâ€“Perot reflection modulators. Journal of Applied Physics, 1992, 72, 855-860.	1.1	23
89	Analysis and optimization of quantumâ€well thickness for GaAs/AlGaAs and InGaAs/GaAs/AlGaAs quantumâ€well lasers. Journal of Applied Physics, 1992, 72, 5047-5054.	1.1	8
90	Demonstration of broadband tunability in a semiconductor laser using sampled gratings. Applied Physics Letters, 1992, 60, 2321-2323.	1.5	81

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91	Efficient vertical-cavity lasers. Optical and Quantum Electronics, 1992, 24, S105-S119.	1.5	29
92	Theoretical gain in compressive and tensile strained InGaAs/InGaAsP quantum wells. Applied Physics Letters, 1991, 59, 588-590.	1.5	45
93	High Performance Quantum Well Asymmetric Fabry-Perot Reflection Modulators: Effect of Layer Thickness Variations. Materials Research Society Symposia Proceedings, 1991, 240, 609.	0.1	1
94	Highâ€contrast, large optical bandwidth fieldâ€induced guide/antiguide modulator. Applied Physics Letters, 1991, 58, 2211-2213.	1.5	8
95	Observation of anomalously large blue shift of the heavyâ€hole photocurrent peak and optical bistability in narrow asymmetric coupled quantum wells. Applied Physics Letters, 1991, 59, 1025-1027.	1.5	15
96	Analysis and optimization of gradedâ€index separateâ€confinement heterostructure waveguides for quantum well lasers. Journal of Applied Physics, 1991, 69, 2857-2861.	1.1	19
97	Large-extinction-ratio, wide-optical-bandwidth field-induced guide/antiguide modulator. , 1991, , .		0
98	Lowâ€threshold highâ€efficiency highâ€yield impurityâ€induced layer disordering laser by selfâ€aligned Siâ€Zn diffusion. Applied Physics Letters, 1990, 57, 2534-2536.	1.5	18
99	Normallyâ€off highâ€contrast asymmetric Fabryâ€“Perot reflection modulator using Wannierâ€“Stark localization in a superlattice. Applied Physics Letters, 1990, 56, 1886-1888.	1.5	57
100	Simultaneous gain and phaseâ€shift enhancements in periodic gain structures. Journal of Applied Physics, 1990, 67, 4387-4389.	1.1	4
101	Asymmetric Fabryâ€“Perot reflection modulators using redâ€and blueâ€shifted electroabsorption effects. Journal of Applied Physics, 1990, 68, 875-877.	1.1	7
102	Generation of picosecond pulses with a gainâ€switched GaAs surfaceâ€emitting laser. Applied Physics Letters, 1990, 57, 963-965.	1.5	33
103	Selfâ€electroâ€optic device based on a superlattice asymmetric Fabryâ€“Perot modulator with an on/off ratio â‰³100:1. Applied Physics Letters, 1990, 57, 1345-1347.	1.5	76
104	Effect of temperature on the operating characteristics of asymmetric Fabryâ€“Perot reflection modulators. Applied Physics Letters, 1990, 57, 267-269.	1.5	21
105	Transverse modulators with a record reflection change of >20%/V using asymmetric Fabryâ€“Perot structures. Applied Physics Letters, 1990, 56, 1626-1628.	1.5	39
106	GaAs/AlGaAs multiple quantum well fieldâ€induced optical waveguide. Applied Physics Letters, 1990, 57, 114-116.	1.5	20
107	Theoretical gain in strained InGaAs/AlGaAs quantum wells including valenceâ€band mixing effects. Applied Physics Letters, 1990, 57, 2835-2837.	1.5	135
108	Comparison of quantumâ€confined Stark effect in interdiffused and abrupt GaAs/AlGaAs quantum wells. Applied Physics Letters, 1989, 55, 2526-2528.	1.5	3

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109	Spontaneous growth of coherent tilted superlattice on vicinal (100)â€‰GaAs substrates. Applied Physics Letters, 1989, 54, 1690-1692.	1.5	105
110	Disordering of GaAs/AlGaAs multiple quantum well structures by thermal annealing for monolithic integration of laser and phase modulator. Applied Physics Letters, 1989, 55, 672-674.	1.5	36
111	Tightâ€binding analysis on exciton binding energy in fieldâ€induced Starkâ€localized superlattices. Applied Physics Letters, 1989, 55, 2002-2004.	1.5	19
112	Optical Anisotropy in a Quantum-Well-Wire Array with Two-Dimensional Quantum Confinement. Physical Review Letters, 1989, 62, 466-469.	2.9	371
113	Wideâ€bandwidth, highâ€efficiency reflection modulators using an unbalanced Fabryâ€“Perot structure. Applied Physics Letters, 1989, 55, 1946-1948.	1.5	25
114	Roomâ€temperature twoâ€dimension exciton exchange and blue shift of absorption edge in GaAs/AlGaAs superlattices under an electric field. Applied Physics Letters, 1989, 54, 1549-1551.	1.5	31
115	Highâ€efficiency TEM00continuousâ€wave (Al,Ga)As epitaxial surfaceâ€emitting lasers and effect of halfâ€wave periodic gain. Applied Physics Letters, 1989, 54, 1209-1211.	1.5	42
116	Optically addressed spatial light modulators by MBE-grown nipi MQW structures. Applied Optics, 1989, 28, 4801.	2.1	16
117	Optically controlled reflection modulator using GaAsâ€“AlGaAs n-i-p-i/multiple-quantum-well structures. Optics Letters, 1989, 14, 230.	1.7	12
118	Relating the chirp parameter to the number of quantum wells in GaAs/AlGaAs waveguide modulators. Applied Physics Letters, 1989, 55, 718-720.	1.5	6
119	Compound-Cavity Lasers For Medium Range Lidar Applications. , 1989, , .		3
120	Extremely wide modulation bandwidth in a low threshold current strained quantum well laser. Applied Physics Letters, 1988, 53, 1378-1380.	1.5	222
121	Use of independently controlled Cl radical and Ar ion beams for anisotropic chemically enhanced etching of GaAs. Applied Physics Letters, 1988, 53, 2308-2310.	1.5	8
122	Impurityâ€inducedâ€disordered phase modulators in AlGaAs/GaAs quantum well and doubleâ€heterostructure waveguides. Applied Physics Letters, 1988, 53, 728-730.	1.5	8
123	Realâ€time technique for the characterization of tunable singleâ€frequency lasers. Applied Physics Letters, 1988, 52, 2217-2219.	1.5	0
124	Selfâ€aligned Siâ€Zn diffusion into GaAs and AlGaAs. Journal of Applied Physics, 1988, 64, 1855-1858.	1.1	7
125	Radical beam/ion beam etching of GaAs. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1988, 6, 1885.	1.6	18
126	Electrically tunable Fabryâ€“Perot mirror using multiple quantum well index modulation. Applied Physics Letters, 1988, 53, 637-639.	1.5	49

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127	Dry Etching and Impurity Diffusion for Integrated Optoelectronics. Materials Research Society Symposia Proceedings, 1988, 126, 237.	0.1	3
128	Design of optimized highâ€speed depletionâ€edgeâ€translation optical waveguide modulators in IIIâ€V semiconductors. Applied Physics Letters, 1987, 51, 792-794.	1.5	24
129	Behavior of SiNxfilms as masks for Zn diffusion. Journal of Applied Physics, 1987, 62, 828-831.	1.1	10
130	Contribution of the bandâ€filling effect to the effective refractiveâ€index change in doubleâ€heterostructure GaAs/AlGaAs phase modulators. Journal of Applied Physics, 1987, 62, 4548-4553.	1.1	25
131	Electrorefraction in GaAs and InGaAsP and its application to phase modulators. Journal of Applied Physics, 1987, 61, 2430-2433.	1.1	65
132	Silicon diffusion into AlxGa1â^'xAs (x=0â€“0.4) from a sputtered silicon film. Applied Physics Letters, 1987, 50, 265-266.	1.5	9
133	Wavelength dependence of high-performance AlGaAs/GaAs depletion-edge-translation waveguide phase modulators. , 1987, , .		1
134	Sputtered silicon as a new etching mask for GaAs devices. Journal of Applied Physics, 1986, 60, 1218-1220.	1.1	3
135	Continuous tunability in threeâ€terminal coupledâ€cavity lasers. Applied Physics Letters, 1986, 48, 1190-1192.	1.5	12
136	Highly efficient waveguide phase modulator for integrated optoelectronics. Applied Physics Letters, 1986, 48, 1243-1245.	1.5	46
137	Reduced dynamic linewidth in threeâ€terminal twoâ€section diode lasers. Applied Physics Letters, 1985, 46, 125-127.	1.5	12
138	Etchedâ€groove coupledâ€cavity vaporâ€phaseâ€transported window lasers at 1.55 Î¼m. Applied Physics Letters, 1985, 46, 5-7.	1.5	10
139	Optimum coupling junction and cavity lengths for coupledâ€cavity semiconductor lasers. Journal of Applied Physics, 1985, 57, 740-754.	1.1	23
140	Continuous operation of monolithic dynamicâ€singleâ€mode coupledâ€cavity lasers. Applied Physics Letters, 1984, 44, 368-370.	1.5	19
141	Optoelectronic properties of coupled cavity semiconductor lasers. Applied Physics Letters, 1984, 44, 735-737.	1.5	8
142	Stabilization and optimum biasing of dynamicâ€singleâ€mode coupledâ€cavity lasers. Applied Physics Letters, 1984, 44, 169-171.	1.5	22
143	Cleavedâ€coupledâ€cavity lasers with large cavity length ratios for enhanced stability. Applied Physics Letters, 1984, 44, 821-823.	1.5	21
144	Verification of coupling gap dependence in coupled-cavity lasers. , 1984, , .		1

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145	On the Formation of Planarâ€Etched Facets in GaInAsPâ€‰/â€‰InP Double Heterostructures. Journal of the Electrochemical Society, 1983, 130, 1918-1926.	1.3	36
146	Singleâ€mode operation of coupledâ€cavity GaInAsP/InP semiconductor lasers. Applied Physics Letters, 1983, 42, 6-8.	1.5	69
147	Analysis of multielement semiconductor lasers. Journal of Applied Physics, 1983, 54, 2962-2969.	1.1	60
148	Directional reactiveâ€ionâ€etching of InP with Cl2 containing gases. Journal of Vacuum Science and Technology, 1981, 19, 225-230.	1.9	54
149	Monolithic twoâ€section GaInAsP/InP activeâ€opticalâ€resonator devices formed by reactive ion etching. Applied Physics Letters, 1981, 38, 315-317.	1.5	140
150	Reactive ion beam etching of InP with Cl2. Applied Physics Letters, 1981, 38, 264-266.	1.5	58
151	GaInAsP/InP stripeâ€geometry laser with a reactiveâ€ionâ€etched facet. Applied Physics Letters, 1980, 37, 681-683.	1.5	108
152	Directional reactive ion etching at oblique angles. Applied Physics Letters, 1980, 36, 583-585.	1.5	67
153	Variable frequency SAW resonators on ferroelectricâ€ferroelastics. Applied Physics Letters, 1978, 32, 129-131.	1.5	11
154	Analog readâ€only memory using gadolinium molybdate. Applied Physics Letters, 1978, 33, 373-375.	1.5	9
155	Electronically variable delay using ferroelasticâ€ferroelectrics. Applied Physics Letters, 1977, 30, 506-508.	1.5	19
156	Zincâ€oxideâ€“onâ€“silicon acoustically scanned imager with positive sensitivity and storage capabilities. Applied Physics Letters, 1975, 27, 6-8.	1.5	21
157	Acoustic waveguide with a cladded core geometry. Applied Physics Letters, 1975, 26, 31-34.	1.5	23
158	Zinc oxide on silicon memory cells scanned by acoustic surface waves. Applied Physics Letters, 1975, 26, 137-139.	1.5	15
159	Effect of bias field in a zincâ€oxideâ€onâ€silicon acoustic convolver. Applied Physics Letters, 1974, 25, 473-475.	1.5	29
160	Interiorâ€surface acoustic waveguiding in capillaries. Applied Physics Letters, 1974, 25, 324-326.	1.5	14
161	cw monolithic acoustic surface wave amplifier incorporated in a Î”v/vwaveguide. Applied Physics Letters, 1973, 23, 117-118.	1.5	23
162	MONOLITHIC ACOUSTIC SURFACEâ€WAVE AMPLIFIER. Applied Physics Letters, 1971, 18, 317-319.	1.5	48

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163	TRAPPING MODEL FOR InSb THIN FILMS. Applied Physics Letters, 1971, 18, 319-321.	1.5	8